

162. The semiconductor structure of claim 161 wherein the monocrystalline insulator layer comprises $\text{Sr}_z\text{Ba}_{1-z}\text{TiO}_3$ where z ranges from 0 to 1.

163. The semiconductor structure of claim 154 wherein the monocrystalline insulator layer comprises an oxide selected from the group consisting of alkaline earth metal zirconates, and alkaline earth metal hafnates and the monocrystalline compound semiconductor layer comprises a material selected from the group consisting of: InP and InGaP.

REMARKS

New claims 144-163 added above find support throughout the specification and in the original claims. See, for example, original claims 1, 8, 25, 26 and 29, as well as the Examples appearing at specification pages 8-12 and the detailed description appearing at pages 13-20. Note also Figure 3 and pages 13-14 in relation to new claim 154. In view of the ample support present herein, no new matter has been entered.

In view of the above amendment Applicant submits that the present application is in condition for examination on the merits, and early notification to this effect is respectfully requested.

Respectfully submitted,

OBLON, SPIVAK, MCCLELLAND,
MAIER & NEUSTADT, P.C.



Richard L. Treanor, Ph.D.
Attorney of Record
Registration No.: 36,379



22850

[illegible]

Claims 144-163 (New)